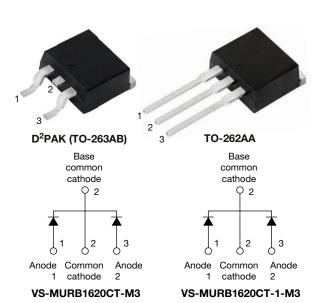
Vishay Semiconductors

Ultrafast Rectifier, 2 x 8 A FRED Pt®



PRIMARY CHARACTERISTICS							
I _{F(AV)}	2 x 8 A						
V _R	200 V						
V _F at I _F	0.895 V						
t _{rr}	35 ns						
T _J max.	175 °C						
Package	D ² PAK (TO-263AB), TO-262AA						
Circuit configuration	Common cathode						

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature



- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RA	ATINGS				
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage		V_{RRM}		200	V
Average rectified forward current	per leg	1		8.0	
Average rectified forward current	total device	I _{F(AV)}	Rated V _R , T _C = 150 °C	16	Α
Non-repetitive peak surge current per leg		I _{FSM}		100	^
Peak repetitive forward current per	leg	I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 150 °C	16	
Operating junction and storage tem	peratures	T _J , T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	Ι _R = 100 μΑ	200	-	-	.,		
Forward voltage	V _F	I _F = 8 A	-	-	0.975	V		
Forward voitage		I _F = 8 A, T _J = 150 °C	-	-	0.895			
Deverage legisers of many		$V_R = V_R$ rated	-	-	5			
Reverse leakage current	I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	-	250	μA		
Junction capacitance	C _T	V _R = 200 V	-	25	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, dI_F/dt =$	$50 \text{ A/}\mu\text{s}, V_{\text{R}} = 30 \text{ V}$	-	-	35			
Reverse recovery time	t _{rr}	I _F = 0.5 A, I _R = 1.0 A, I _{REC} = 0.25 A		-	-	25			
		T _J = 25 °C	I _F = 8 A	-	20	-	ns - A - nC		
		T _J = 125 °C		-	34	-			
Dook roomsons current	I _{RRM}	T _J = 25 °C		=	1.7	-			
Peak recovery current		T _J = 125 °C	dl _F /dt = 200 A/μs V _R = 160 V	-	4.2	-			
Reverse recovery charge	Q _{rr}	T _J = 25 °C	VR = 100 V	-	23	-			
		T _J = 125 °C		=	75	-	110		

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C		
Thermal resistance, junction-to-case per leg	R _{thJC}		-	-	3.0			
Thermal resistance, junction-to-ambient per leg	R _{thJA}		-	-	50	°C/W		
Thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-			
Weight			-	2.0	-	g		
vveigni			-	0.07	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking daying		Case style D ² PAK (TO-263AB)		MURB	1620CT			
Marking device		Case style TO-262		MURB1	620CT-1			

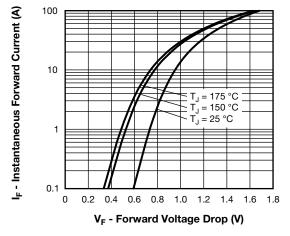


Fig. 1 - Typical Forward Voltage Drop Characteristics

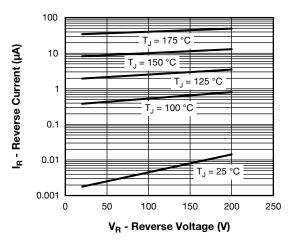


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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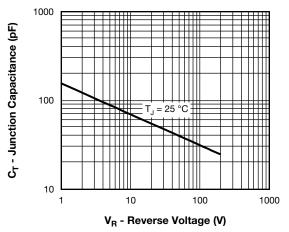


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

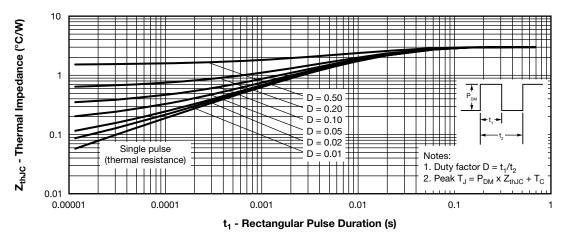


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

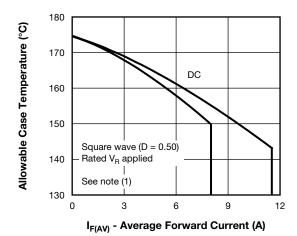


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

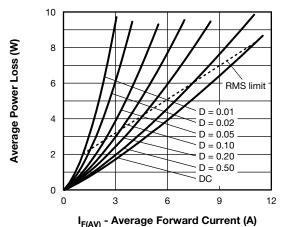


Fig. 6 - Forward Power Loss Characteristics

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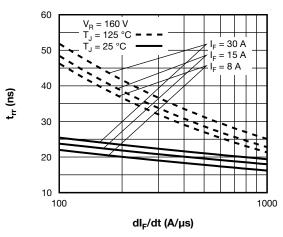


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

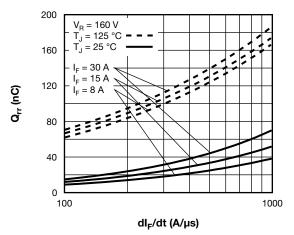
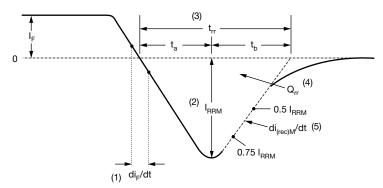


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D)}; I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

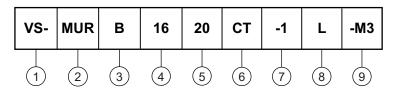
(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Ultrafast MUR series

- Current rating (16 = 16 A)

5 - Voltage rating (20 = 200 V)

- CT = center tap (dual)

7 • None = D²PAK (TO-263AB)

• -1 = TO-262AA

None = tube (50 pieces)

• L = tape and reel (left oriented, for D²PAK (TO-263AB) package)

• R = tape and reel (right oriented, for D²PAK (TO-263AB) package)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

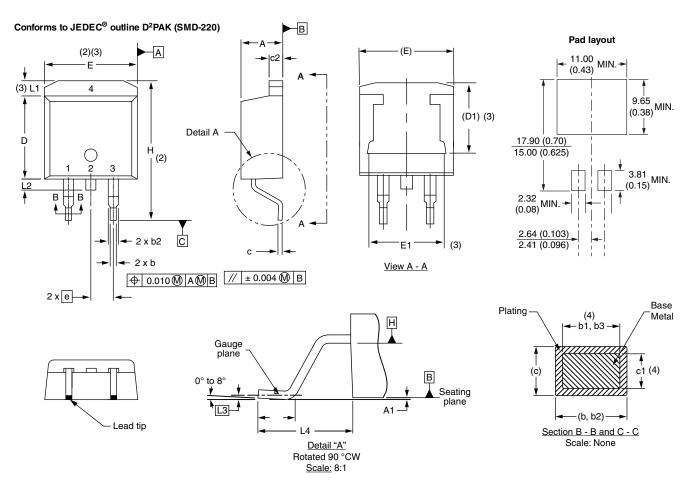
LINKS TO RELATED DOCUMENTS							
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?96164					
Dimensions	TO-262AA	www.vishay.com/doc?96165					
Part marking information -	D ² PAK (TO-263AB)	www.vishay.com/doc?95444					
	TO-262AA	www.vishay.com/doc?95443					
Packaging information	D ² PAK (TO-263AB)	www.vishay.com/doc?96424					



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL MILLIM	ETERS	INCHES		NOTES	SYMBOL		MILLIMETERS		INCHES			
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES		STWIDGE	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164

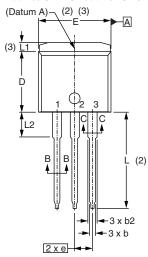


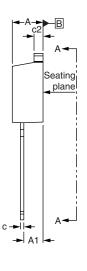
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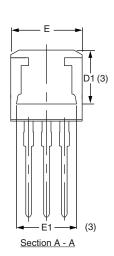
TO-262AA

DIMENSIONS in millimeters and inches

Modified JEDEC® outline TO-262







⊕ 0.010 **M** A**M** B

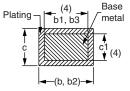
Lead assignments



Diodes 1. - Anode (two die)/open (one die)

2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

SYMBOL	MILLIM	IETERS	INC	INCHES			
	MIN.	MAX.	MIN.	MAX.	NOTES		
Α	4.06	4.83	0.160	0.190			
A1	2.03	3.02	0.080	0.119			
b	0.51	0.99	0.020	0.039			
b1	0.51	0.89	0.020	0.035	4		
b2	1.14	1.78	0.045	0.070			
b3	1.14	1.73	0.045	0.068	4		
С	0.38	0.74	0.015	0.029			
c1	0.38	0.58	0.015	0.023	4		
c2	1.14	1.65	0.045	0.065			
D	8.51	9.65	0.335	0.380	2		
D1	6.86	8.00	0.270	0.315	3		
Е	9.65	10.67	0.380	0.420	2, 3		
E1	7.90	8.80	0.311	0.346	3		
е	2.54	2.54 BSC		0 BSC			
L	13.46	14.10	0.530	0.555			
L1	-	1.65	-	0.065	3		
L2	3.56	3.71	0.140	0.146			

Notes

(4) Dimension b1 and c1 apply to base metal only

Controlling dimension: inches

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)



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